



# SANYO Semiconductors

## DATA SHEET

# CPH6429

 — N-Channel Silicon MOSFET  
**Ultrahigh-Speed Switching Applications**

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		2	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	8	A
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	1.8	3.6		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =4V		170	220	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		190	270	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz		325		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz		29		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz		21		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit		11		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		17		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit		40		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		27		ns

Marking : ZF

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**SANYO Electric Co.,Ltd. Semiconductor Company**

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# CPH6429

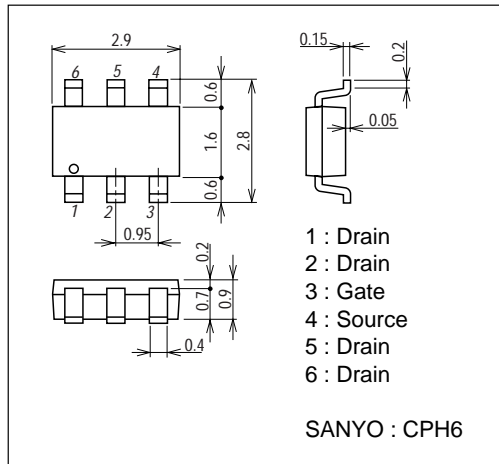
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	$V_{DS}=30V, V_{GS}=4V, I_D=2A$		4.2		nC
Gate-to-Source Charge	Qgs	$V_{DS}=30V, V_{GS}=4V, I_D=2A$		1.1		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=30V, V_{GS}=4V, I_D=2A$		1.1		nC
Diode Forward Voltage	VSD	$I_S=2A, V_{GS}=0$		0.86	1.2	V

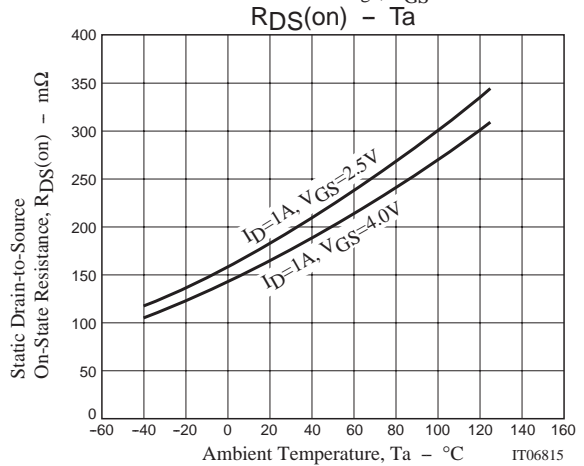
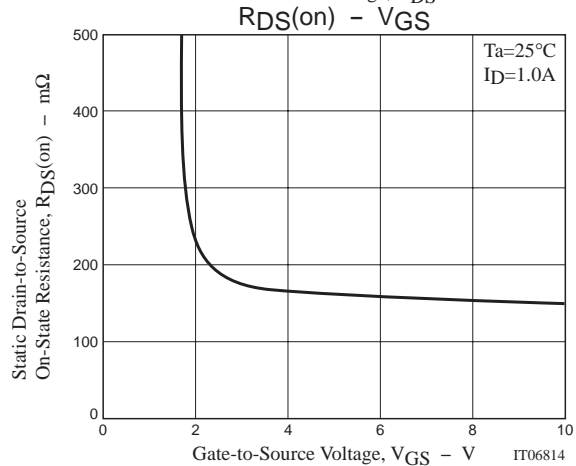
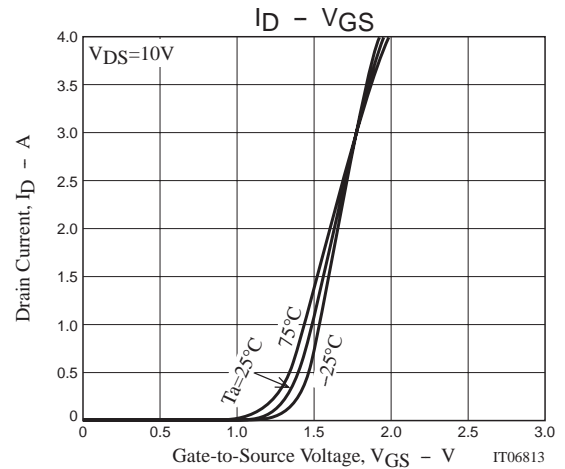
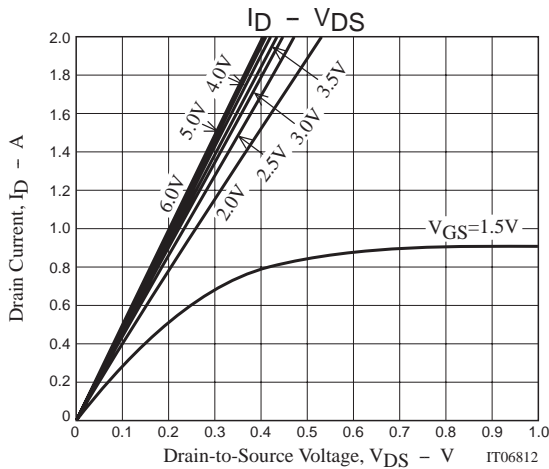
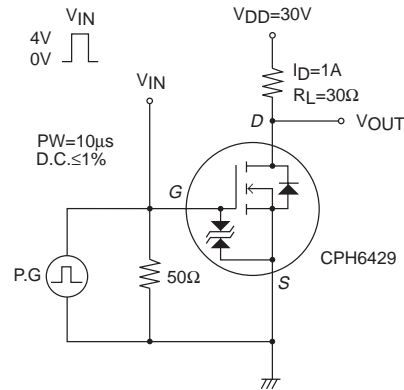
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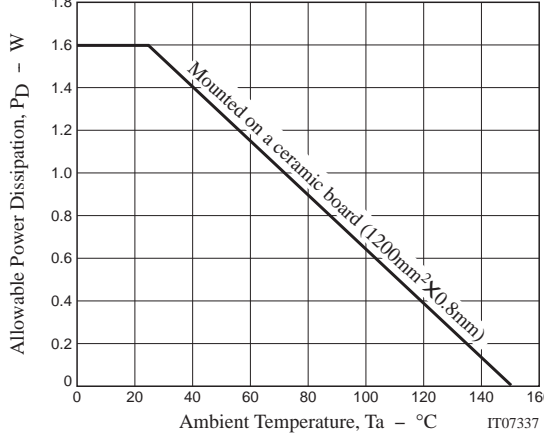
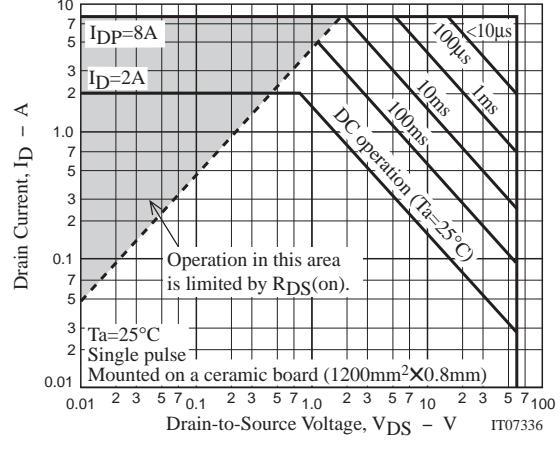
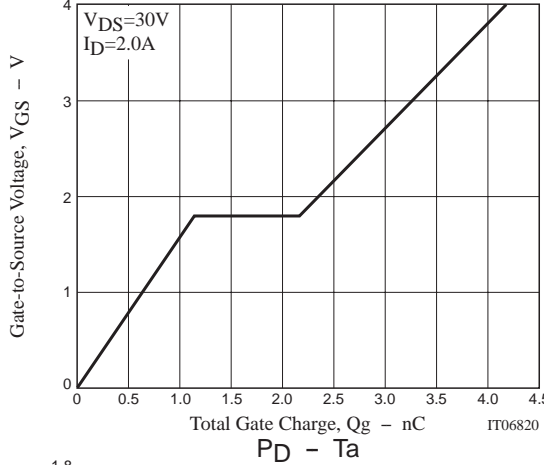
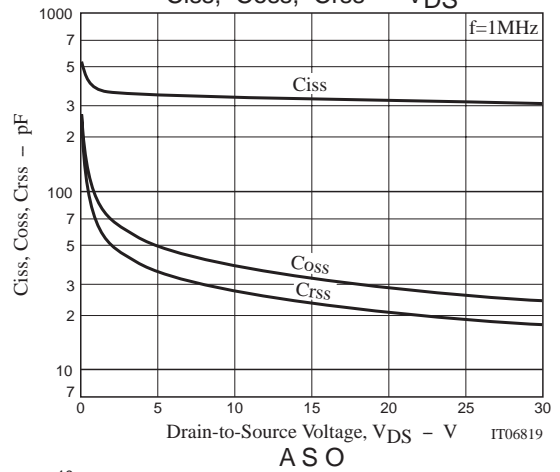
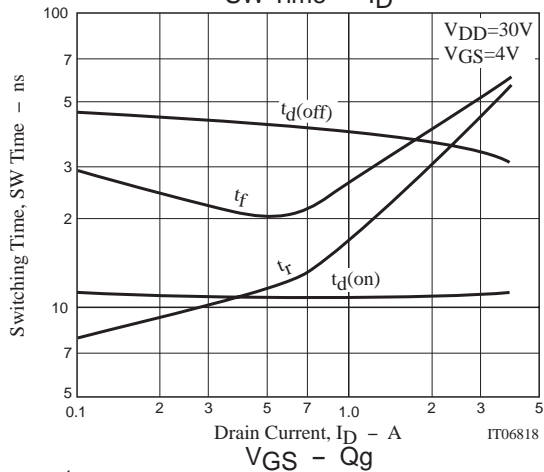
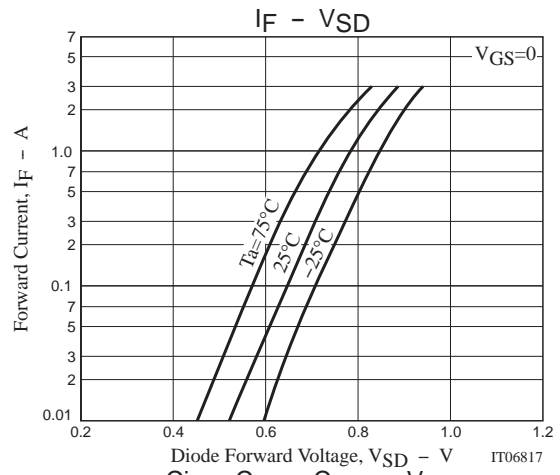
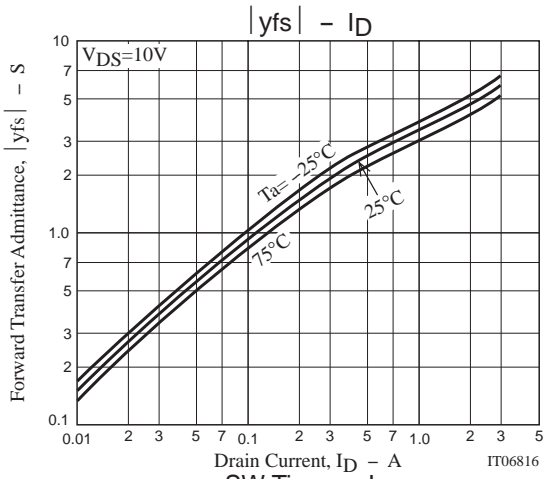
unit : mm

2151A



## Switching Time Test Circuit





Note on usage : Since the CPH6429 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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